

Atty. Docket No. OPP031051US  
Serial No: 10/722,295

Amendment to the Specification

Please replace paragraph [0015] at p. 4, l. 16-p. 5, l. 3, with the following paragraph:

[0015] After forming a polish stop layer on a semiconductor substrate, an anti-reflection coating is formed on the polish stop layer, and the anti-reflection coating is selectively etched to form an anti-reflection coating pattern. An area of the polish stop layer exposed through the anti-reflection coating pattern and the semiconductor substrate to a predetermined depth are etched to form the trench, and ends of the anti-reflection coating pattern and ends of the polish stop layer under the ends of the anti-reflection coating pattern are etched such that the ends of the anti-reflection coating are formed into a rounded configuration (see anti-reflection coating 14 in FIG. 2E).

Please replace paragraph [0021] at p. 6, ll. 2-4, with the following paragraph:

[0021] FIGS. 2a2A through 2d2E are sectional views used to describe a method for forming a trench in a semiconductor device according to an exemplary embodiment of the present invention.

Please replace paragraph [0023] at p. 6, ll. 8-10, with the following paragraph:

[0023] FIGS. 2a2A through 2d2E are sectional views used to describe a method for forming a trench in a semiconductor device according to an exemplary embodiment of the present invention.